

IFN147

N-Channel Silicon Junction Field-Effect Transistor

- Low-Noise Audio Amplifier
- Equivalent to Japanese 2SK147

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Reverse Gate Drain Voltage	- 40 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	300 mW
Power Derating	2.4 mW/ $^\circ\text{C}$

At 25°C free air temperature:

Static Electrical Characteristics

		IFN147			Process NJ450	
		Min	Typ	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	$V_{(\text{BR})\text{GSS}}$	- 40			V	$I_G = - 1 \mu\text{A}, V_{\text{DS}} = \emptyset\text{V}$
Gate Reverse Current	I_{GSS}			- 1	nA	$V_{\text{GS}} = - 30\text{V}, V_{\text{DS}} = \emptyset\text{V}$
				- 1	μA	$V_{\text{GS}} = - 30\text{V}, V_{\text{DS}} = \emptyset\text{V}$
Gate Source Cutoff Voltage	$V_{\text{GS}(\text{OFF})}$	- 0.3		- 1.2	V	$V_{\text{DS}} = 10\text{V}, I_D = 1 \mu\text{A}$
Drain Saturation Current (Pulsed)	I_{DSS}	5		30	mA	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = \emptyset\text{V}$

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	30	40		mS	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = \emptyset\text{V}$ $I_{\text{DSS}} = 5 \text{ mA}$	f = 1 kHz
Common Source Input Capacitance	C_{iss}			75	pF	$V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = \emptyset\text{V}$	f = 1 kHz
Common Source Reverse Transfer Capacitance	C_{rss}			15	pF	$V_{\text{DS}} = 10\text{V}, I_D = \emptyset$	f = 1 Hz
Noise Figure	NF		1		dB	$V_{\text{DS}} = 10\text{V}, I_D = 5 \text{ mA}$	f = 1 kHz
				10	dB	$R_G = 100\Omega$	f = 100 Hz

TO-18 Package
Dimensions in Inches (mm)

Pin Configuration
1 Source, 2 Gate & Case, 3 Drain